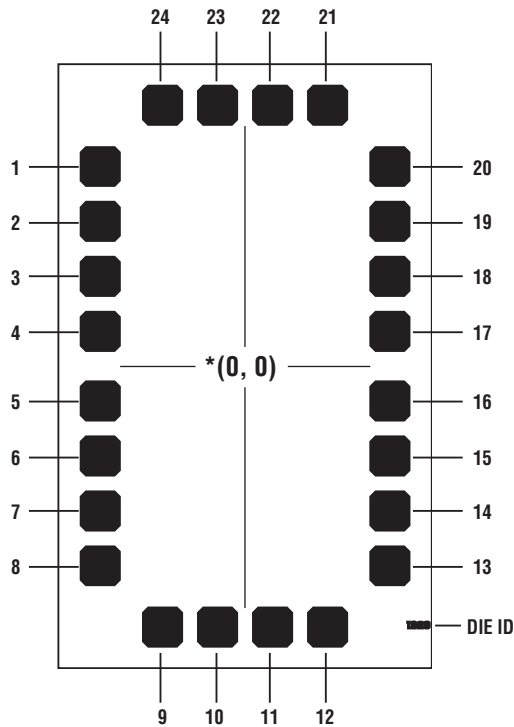


## Four-Channel Multiplexed Transimpedance Amplifier with Output Multiplexing



Die Size: 36mils (914.4 $\mu$ m) $\times$  55mils (1397 $\mu$ m)  
 Bond Pad Size: 4mils (102 $\mu$ m) $\times$  4mils (102 $\mu$ m)  
 Bond Pad Opening: 3.2mils (82 $\mu$ m) $\times$  3.2mils (82 $\mu$ m)  
 Bond Pad Metal Thickness: 0.29mils (7.4 $\mu$ m)  
 Wafer Saw Street Width: 2.4mils (61 $\mu$ m)  
 Wafer/Die Thickness: 8mils (200 $\mu$ m)  
 Backside Metal: None  
 Backside Potential: V<sup>-</sup>

PAD #	PAD NAME	X COORDINATE ( $\mu$ m)	Y COORDINATE ( $\mu$ m)
1	CHSEL1	417.9	303.24
2	V <sub>CC0</sub>	302.9	303.24
3	CHSEL0	187.9	303.24
4	V <sub>CC1</sub>	72.9	303.24
5	V <sub>REF1</sub>	-72.9	303.24
6	GND	-187.9	303.24
7	IN1	-302.9	303.24
8	GND	-417.9	303.24
9	IN2	-546.21	172.5
10	V <sub>REF2</sub>	-546.21	57.5
11	V <sub>REF3</sub>	-546.21	-57.5
12	IN3	-546.21	-172.5
13	GND	-417.9	-303.24
14	IN4	-302.9	-303.24
15	GND	-187.9	-303.24
16	V <sub>REF4</sub>	-72.9	-303.24
17	V <sub>CC2</sub>	72.9	-303.24
18	O_MUX	187.9	-303.24
19	V <sub>CC0</sub>	302.9	-303.24
20	DNC	417.9	-303.24
21	OUTTERM	546.21	-172.5
22	GND	546.21	-57.5
23	GND	546.21	57.5
24	OUT	546.21	172.5

\*Die center coordinate (0, 0)

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## FEATURES

- 220MHz -3dB Bandwidth with 2pF Input Capacitance
- Single-Ended Output
- 74k $\Omega$  Transimpedance Gain
- 4.8pA/ $\sqrt{\text{Hz}}$  Input Current Noise Density at 200MHz (2pF)
- 64nA<sub>RMS</sub> Integrated Input Current Noise Over 200MHz (2pF)
- Linear Input Range 0 $\mu$ A to 30 $\mu$ A
- Overload Current >  $\pm$ 400mA Peak
- Fast Overload Recovery 12ns, 1mA
- Fast Channel Switchover < 50ns
- Single 5V Supply
- 200mW Power Dissipation for 4 Channels
- 2V<sub>p-p</sub> Output Swing on 100 $\Omega$  Load
- Output MUX Combines Multiple 4-Channel Devices to Create 4, 8, 12, 16, 24, 32 Channel Solutions

## APPLICATIONS

- LIDAR Receiver
- Industrial Imaging

# LTC6561 DICE/DWF

## DESCRIPTION

The LTC<sup>®</sup>6561 is a low-noise, four-channel, transimpedance amplifier (TIA) with 220MHz bandwidth. The LTC6561 multi-channel transimpedance amplifier's low noise, high transimpedance, and low power dissipation are ideal for LIDAR receivers using Avalanche Photodiodes (APDs). The amplifier features 74k $\Omega$  transimpedance gain and 30 $\mu$ A linear input current range. Using an APD input circuit with a total capacitance of 2pF, the input current noise density is 4.8pA/ $\sqrt{\text{Hz}}$  at 200MHz. With lower capacitance, noise and bandwidth improve further. Only a 5V single supply

is needed and the device consumes only 200mW. Utilizing the internal 4-to-1 MUX along with the LTC6561's output MUX; multiple 4-channel LTC6561 devices can be combined to directly interface with 12-, 16- and 32-channel APD arrays. The LTC6561's fast overload recovery and fast channel switchover make it well suited for LIDAR receivers with multiple APDs. Its single-ended output can swing 2V<sub>P-P</sub> on a 100 $\Omega$  load while its low impedance op amp style output can drive back-terminated 50 $\Omega$  cables.

## ABSOLUTE MAXIMUM RATINGS (Note 1)

Total Supply Voltage ( $V_{CC1}$ ,  $V_{CC2}$ ,  $V_{CC0}$  to GND).....5.5V  
 Input Voltage (CHSEL0, CHSEL1, O\_MUX).....-0.3V to 5.5V  
 Amplifier Reference Current ( $V_{REF1}$ ,  $V_{REF2}$ ,  $V_{REF3}$ ,  $V_{REF4}$ )..... $\pm$ 10mA  
 Amplifier Input Current (IN1, IN2, IN3, IN4) .....  $\pm$ 400mA RMS  $\pm$ 2A Transient (10ns)

Amplifier Output Current (OUT, OUTTERM).....+80mA  
 Operating Temperature Range  
 LTC6561.....-40 $^{\circ}$ C to 125 $^{\circ}$ C  
 Storage Temperature Range.....-65 $^{\circ}$ C to 150 $^{\circ}$ C  
 Junction Temperature ..... 150 $^{\circ}$ C

## DIE CROSS REFERENCE

FINISHED PART NUMBER	ORDER PART NUMBER
LTC6561	LTC6561 DICE/DWF

Please refer to ADI standard LTC6561 product data sheet for other applicable product information and typical performance information.

## AC ELECTRICAL CHARACTERISTICS $T_A = 25^{\circ}\text{C}$ , $V_{CC1,2} = V_{CC0} = 5\text{V}$ , $O\_MUX = 0\text{V}$ , $\text{GND} = 0\text{V}$ , $Z_{\text{LOAD}} = 100\Omega$ . Output taken from OUT pin.

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
BW	-3dB Bandwidth	200mV <sub>P-ROUT</sub> and $C_{\text{IN,TOT}} = 2\text{pF}$		220		MHz
$R_T$	Small Signal Transimpedance	$I_{\text{IN}} < 2\mu\text{A}_{\text{P-P}}$	63	74	85	k $\Omega$
$R_{\text{IN}}$	Input Resistance	$f = 100\text{kHz}$		236		$\Omega$
$R_{\text{OUT}}$	Output Resistance	$f = 100\text{kHz}$		3		$\Omega$
$I_n$	Input Current Noise Density	$f = 100\text{MHz}$ , $C_{\text{IN,TOT}} = 2\text{pF}$		4.3		pA/ $\sqrt{\text{Hz}}$
		$f = 200\text{MHz}$ , $C_{\text{IN,TOT}} = 2\text{pF}$		4.8		pA/ $\sqrt{\text{Hz}}$
	Integrated Input Current Noise	$f = 0.1\text{MHz}$ to 100MHz, $C_{\text{IN,TOT}} = 2\text{pF}$		43		nA <sub>RMS</sub>
		$f = 0.1\text{MHz}$ to 200MHz, $C_{\text{IN,TOT}} = 2\text{pF}$		64		nA <sub>RMS</sub>
	Adjacent Channel to Channel Isolation	$f = 100\text{MHz}$		-45		dB
	Non Adjacent Channel Isolation	$f = 100\text{MHz}$		-65		dB
$t_{\text{RECOVER}}$	Overload Recovery Time	Input Pulse <1mA		12		ns
$t_{\text{SWITCH}}$	Channel Switchover Time			50		ns

## DC ELECTRICAL CHARACTERISTICS

$T_A = 25^\circ\text{C}$ ,  $V_{CC1,2} = V_{CC0} = 5\text{V}$ ,  $O\_MUX = 0\text{V}$ ,  $\text{GND} = 0\text{V}$ ,  $Z_{\text{LOAD}} = 100\Omega$ .  
Output taken from OUT pin.

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
<b>IN1,2,3,4 Pins and <math>V_{\text{REF}1,2,3,4}</math> Pins</b>						
$V_{\text{IN}}$	Input Bias Voltage	Active Channel	1.43	1.55	1.64	V
		Inactive Channel	0.78	0.93	1.38	V
$V_{\text{REF}}$	Input Reference Voltage	Active Channel	1.43	1.55	1.63	V
		Inactive Channel	1.34	1.50	1.67	V
Offset	$V_{\text{IN}} - V_{\text{REF}}$	Active Channel	-12		12	mV
		Inactive Channel	-741		-116	mV
<b>OUT Pin</b>						
$V_{\text{OUT}}$	Output Default Voltage	$O\_MUX = 0\text{V}$ (Output Enabled)	0.83	1.10	1.47	V
		$O\_MUX = 3.3\text{V}$ , Standalone Device	0.32	0.60	0.88	V
OVR	Output Voltage Range	$I_{\text{IN}}$ Current Range = 0 to $-50\mu\text{A}$	1.22	1.90	2.58	$V_{\text{P-P}}$
OUTTERM	Internal Series Resistor for Optional Output		44	56	70.8	$\Omega$
<b>CHSEL0, CHSEL1, <math>O\_MUX</math> Pins with Internal Pull-Down Resistors</b>						
$V_{\text{IL}}$					0.7	V
$V_{\text{IH}}$			1.5			V
$I_{\text{IL}}$	Pin Voltage = 0.7V		16.9	20.7	26.0	$\mu\text{A}$
$I_{\text{IH}}$	Pin Voltage = 1.5V		37	47	57	$\mu\text{A}$
$C_{\text{IN}}$				1.5		pF
$R_{\text{IN}}$			22	29	35	$\text{k}\Omega$
<b>Power Supply</b>						
$V_{\text{S}}$	Operating Supply Range		4.75	5	5.25	V
$I_{\text{CC}1,2}$	Input Supply Current	$V_{\text{CC}1}$ & $V_{\text{CC}2}$ are Internally Tied Together	29	36.3	44	mA
$I_{\text{CC}0}$	Output Supply Current	Both $V_{\text{CC}0}$ Pins are Internally Tied Together	1.8	2.3	2.8	mA
$I_{\text{S}}$	Total Supply Current ( $I_{\text{S}(V_{\text{CC}1,2})} + I_{\text{S}(V_{\text{CC}0})}$ )		30.8	38.6	46.8	mA
PSRR( $V_{\text{CC}1,2}$ )	Input Power Supply Rejection Ratio	$V_{\text{CC}1,2} = 4.75\text{V}$ to $5.25\text{V}$ , $V_{\text{CC}0} = 5\text{V}$	21	25		dB
PSRR( $V_{\text{CC}0}$ )	Output Power Supply Rejection Ratio	$V_{\text{CC}0} = 4.75\text{V}$ to $5.25\text{V}$ , $V_{\text{CC}1,2} = 5\text{V}$	34	40		dB

**Note 1:** Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

**Note 2:** All measurement were conducted in the dark.

## PAD FUNCTIONS

**CHSEL1:** MSB for Channel Selection. CMOS input. The CHSEL1 pad has a 29kΩ internal pull-down resistor. Default value is 0V.

**V<sub>CC0</sub>:** Positive Power Supply for the Output Stage. Typically 5V. V<sub>CC0</sub> can be tied to V<sub>CC1</sub> or V<sub>CC2</sub> for single supply operation. Between the positive supply and ground, bypass capacitors of 1000pF and 0.1μF should be placed as close to the part as possible. V<sub>CC0</sub> pads are internally tied together.

**CHSEL0:** LSB for Channel Selection. CMOS input. The CHSEL0 pad has a 29kΩ internal pull-down resistor. Default value is 0V.

**V<sub>CC1</sub>, V<sub>CC2</sub>:** Positive Power Supply. Typically 5V. Between the positive supply and ground, bypass capacitors of 1000pF and 0.1μF should be placed as close to the part as possible. V<sub>CC1</sub> and V<sub>CC2</sub> are internally tied together.

**V<sub>REF1</sub>, V<sub>REF2</sub>, V<sub>REF3</sub>, V<sub>REF4</sub>:** Reference Voltage Pad for Transimpedance Amplifier in Channel 1, 2, 3, and 4 Respectively. This pad sets the input DC voltage for each transimpedance amplifier. The V<sub>REF</sub> pad has a Thevenin equivalent resistance of approximately 1.4k and can be overdriven by an external voltage. If no voltage is applied

to V<sub>REF</sub>, it will float to a default voltage of approximately 1.55V on a 5V supply. Each V<sub>REF</sub> pad should be bypassed with a high quality ceramic bypass capacitor of at least 0.1μF. The bypass cap should be located close to its V<sub>REF</sub> pad.

**GND:** Negative Power Supply. Normally tied to ground.

**IN1, IN2, IN3, IN4:** Input Pad for Transimpedance Amplifier for Channels 1, 2, 3, and 4 Respectively. This pad is internally biased to 1.55V.

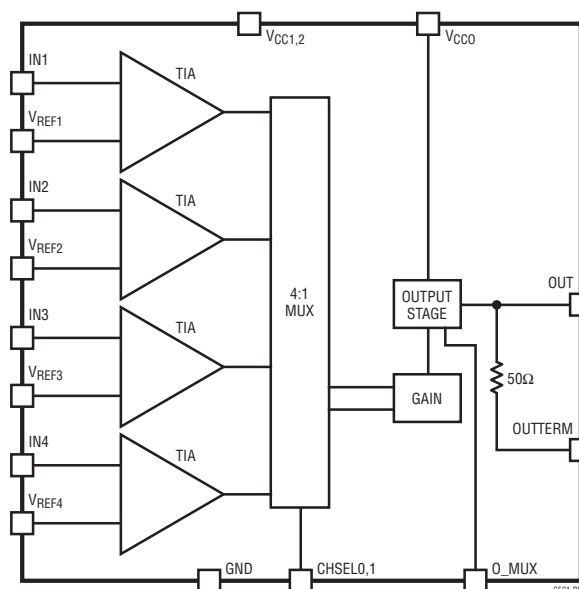
**O\_MUX:** Output MUX. CMOS Input. This pad is functional when multiple LTC6561s are combined at the output. When O\_MUX is low, the output is enabled. When O\_MUX is high, all 4 inputs are decoupled from the output. Default value is 0V. This MUX pad is ineffective unless a 2nd LTC6561 is DC-coupled at the output. See Applications section on how to use O\_MUX to expand the channel count with multiple LTC6561's. The O\_MUX pad has a 29kΩ internal pull-down resistor.

**DNC:** Do not connect.

**OUTTERM:** TIA Output with an Internal Series 50Ω Resistor.

**OUT:** TIA Output without an internal series 50Ω Resistor.

## BLOCK DIAGRAM



Wafer level testing is performed per indicated specifications for dice. Considerable differences in performance can often be observed for dice versus packaged units due to the influences of packaging and assembly on certain devices and/or parameters. Please consult factory for more information on dice performance and lot qualifications via lot sampling test procedures.

Dice data sheet subject to change. Please consult factory for current revision in production.